IEEE SW Test Workshop Semiconductor Wafer Test Workshop

June 6 to 9, 2010 San Diego, CA



Wafer Level ESD Probe Card Solutions



Grund Technical Solutions, LLC Authors: Evan Grund Jay Thomas

Agenda

- Review of advances in ESD waveforms required for wafer-level scribeline test
- Challenges related to full TEG pattern automation of ESD test structures
- Solutions for combining full DC and ESD parametric testing in a single touchdown
- Conclusions



Evolving Parametric Test Probing





June 6 to 9, 2010

ESD Scribeline Tests

• Similar to HF-PIV for power transistor characterization

Туре	Device	Freq	Matrix	Test Name
IV	Transistor	1 MHz	10 MHz	Vt, Gm, Vsat, BV, IDVD, IDVG, Gate & Drain Leakage, V-ramp, J-ramp, TDDB, HCI, Charge Pump, EM
CV	Transistor	1	10	Thick Gate Tox, Field Tox, Diffusion Profiles, Trapped
	Oxide	MHz	MHz	Charge, Mobile Ion, C-gate, C-drain
HF-CV	Transistor Oxide	100 MHz	1 GHz	Thin Gate Tox, Carrier Life Time, Contamination
HF-PIV	Power	200	1	Vt, Gm, Vsat, IDVD, IDVG, Gate Charge, Trapped
	Transistor	MHz	GHz	Charge, CMOS Latch-up (I/O Structure)
ESD	ESD	200	1	TLP, HBM, MM, HMM (IEC 61000-4-2), WCDM,
	structure	MHz	GHz	TDB(time dependent breakdown) , Leakage curves
Flash	Transistor	200	1	State 0-State 1 Programming Current/Time, Read
R-ram	Resistor	MHz	GHz	Leakage Current



ESD Waveforms

- TLP Transmission Line Pulse
- HBM Human Body Model
- CDM Charge Device Model
- WCDM Wafer Charged Device Model
- MM Machine Model
- HMM Human Metal Model (IEC 61000-4-2)



TLP & VFTLP Waveforms

TLP - Transmission Line Pulse

- Used for characterization of a ESD structure to a constant voltage pulse
- Not used for simulating ESD events
- Pulse delivery can be by a probe card

• VFTLP – Very Fast Transmission Line Pulse

- Can characterize ESD structures designed for fastest (CDM) protection
- Pulse delivery by manual RF probes

10mA -10A into 50Ω 100nS wide

10mA -20A into 50Ω 1-10nS wide





HBM (Human Body Model)





• Created by an RC discharge

- Clean PIV waveforms showing turn-on response are possible at the wafer level
 - Not seen by TLP
 - Not seen at package level



Example of an I-V Curve from a single HBM pulse



HBM Flying Probe Test System

- ESD testing on wafers, bare die, and packaged parts
- Eliminate parasitic distortions in relay-base test systems
- TLP-like measurements of actual DUT pin response



TDR pod for sensing pulse response at the DUT pads



June 6 to 9, 2010

CDM (Charge Device Model)

- Top ground plane is lowered until pogo pin contact DUT pin
- Discharge path is from charged DUT to grounded pogo pin



WCDM (Wafer Charge Device Model)

- Discharge path of metal disk is through a single probe (red)
- CDM spark occurs as disk is lowered to make probe contact





June 6 to 9, 2010

WCDM (Wafer Charge Device Model)

- Two WCDM boards scaled for 5pF and 15pF capacitance
- This simulates small & large package cap. in CDM tests
- Discharge is thru a cantilever tungsten probe tip







June 6 to 9, 2010

MM (Machine Model)



- Under-damped sine wave
- Waveform created by parasitic inductance
- Not the best waveform for wafer-level test !



-2



June 6 to 9, 2010

Comparison – CDM, MM, HBM

- Short pulses produce pin holes and cratering
- Longer pulse waveforms cause melting

MM, HBM





June 6 to 9, 2010

HMM (Human Metal Model)

- Simulates ESD short & long pulse effects; IEC 61000-4-2
- Use a 50Ω pulse delivery at wafer-level; *Not* the Gun!



ESD-TDB (Time Dependent Breakdown)

Toshiba Example (very similar to TDDB)

Low voltage CDM investigation

Dec 2008 – Nozomu Kawai, Nobuyuki Wakai

- < 500V VF-TLP pulse stream on wafer</p>
- Monitor leakage degradation (wear out)
- Same test methodology could be applied to standard TLP or HBM pulse streams.





June 6 to 9, 2010

ESD Pulse Delivery With Full DC Parametric Analysis



3-D Views of Genus Probe Card/Matrix



24 Pin DC + HBM Automation Precise PIV characterization – data points every 200ps



18

Calibration Is A Big Issue

System Corrections

- Open & Short calibration required
- Shorting structure tested at low & high power
- Oscilloscope gain & offset correction
- Inductive current sensor linearity correction
- Multiple pin interaction corrections
- Non-Kelvin correction for contact resistance
- Kelvin correction for sense high impedance attenuation

Each raw data point gathered is process by complex vector math equations to account accurately for all correction factors.



Kelvin TDR Waveforms

- TLP pulse is delivered with high current force probes
- Separate sense probes measure differential voltage





June 6 to 9, 2010

Performance of TDT and Kelvin

- Measured with 1.2nS pulses
- Kelvin removes the variation of contact resistances





June 6 to 9, 2010

Conclusions

- Automated ESD scribeline test is now a reality
 - TLP, HBM, HMM, WCDM, Pulse IV Curve Tracing
 - These tests can be combined with traditional parametric test suites for single touch down characterization

• Challenges to full TEG automation are solvable

- WCDM & VFTLP are constrained to one or two pins
- Most ESD tests can be automated for full parametric
 TEG testing using the Genus probe card/switch matrices
- Sophisticated calibration routines maintain accurate measurements at all probe card needles
- Modular design of matrices adapt to future test needs

